

BF721T1

Preferred Device

PNP Silicon Transistor

Features

- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-300	Vdc
Collector-Base Voltage	V_{CBO}	-300	Vdc
Collector-Emitter Voltage	V_{CER}	-300	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current	I_C	-50	mAdc
Total Power Dissipation up to $T_A = 25^\circ\text{C}$ (Note 1)	P_D	1.5	W
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	83.3	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 in².

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I _C = -1.0 mA, I _B = 0)	V _{(BR)CEO}	-300	-	Vdc
Collector-Base Breakdown Voltage (I _C = -100 μA, I _E = 0)	V _{(BR)CBO}	-300	-	Vdc
Collector-Emitter Breakdown Voltage (I _C = -100 μA, R _{BE} = 2.7 kΩ)	V _{(BR)CER}	-300	-	Vdc
Emitter-Base Breakdown Voltage (I _E = -10 μA, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector-Base Cutoff Current (V _{CB} = -200 Vdc, I _E = 0)	I _{CBO}	-	-10	nA
Collector-Emitter Cutoff Current (V _{CE} = -250 Vdc, R _{BE} = 2.7 kΩ) (V _{CE} = -200 Vdc, R _{BE} = 2.7 kΩ, T _J = 150°C)	I _{CER}	-	-50 -10	nA μA
ON CHARACTERISTICS				
DC Current Gain (I _C = -25 mA, V _{CE} = -20 Vdc)	h _{FE}	50	-	-
Collector-Emitter Saturation Voltage (I _C = -30 mA, I _B = -5.0 mA)	V _{CE(sat)}	-	-0.8	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product (V _{CE} = -10 Vdc, I _C = -10 mA, f = 35 MHz)	f _T	60	-	MHz
Feedback Capacitance (V _{CE} = -30 Vdc, I _C = 0, f = 1.0 MHz)	C _{re}	-	1.6	pF

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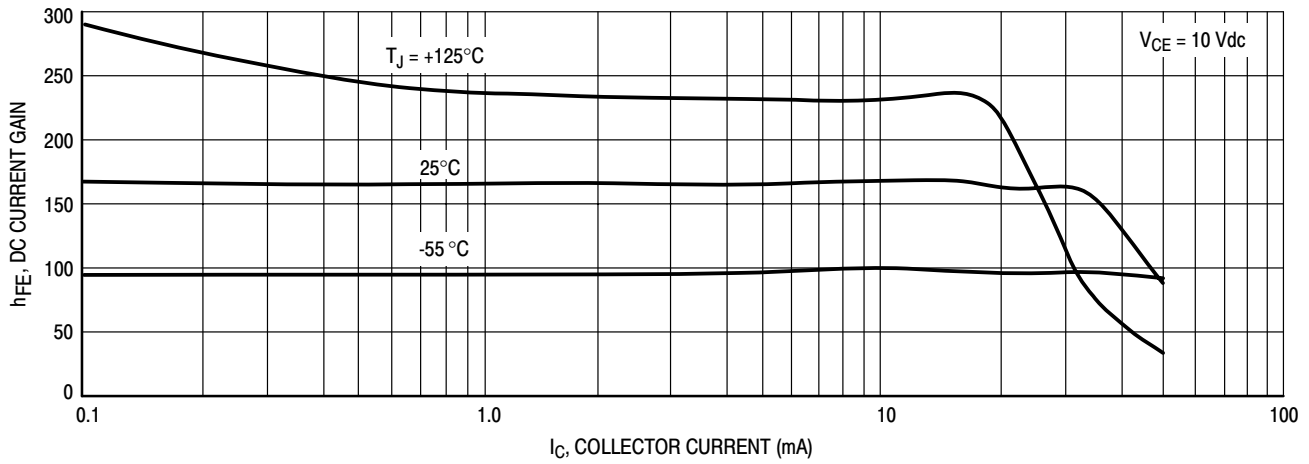


Figure 1. DC Current Gain

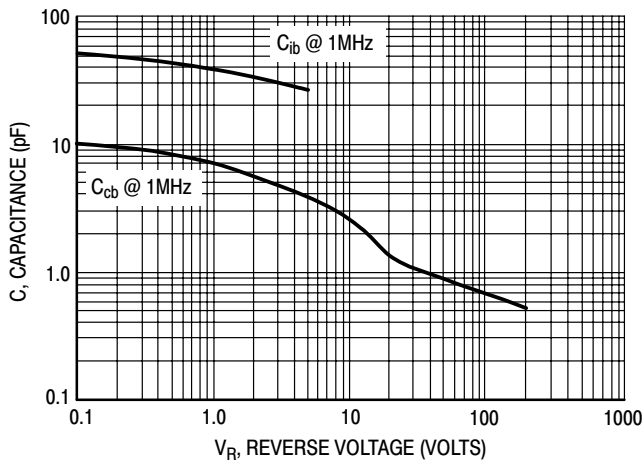


Figure 2. Capacitance

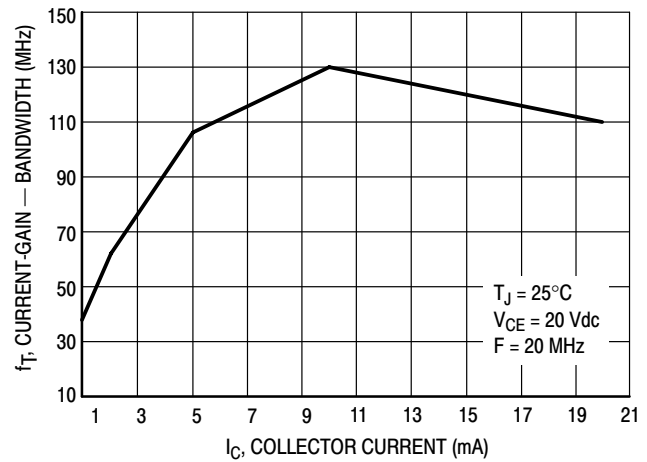


Figure 3. Current-Gain — Bandwidth

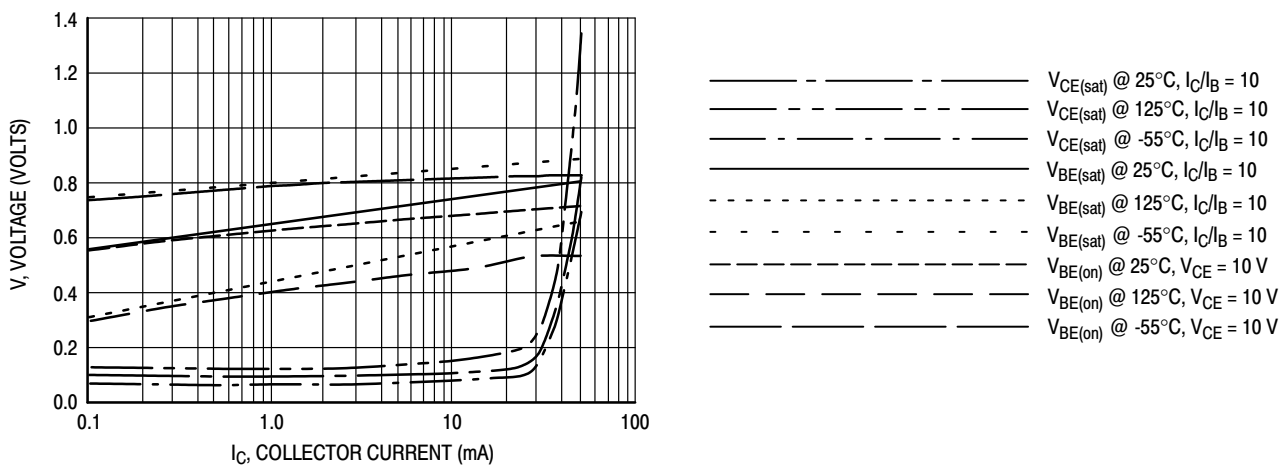
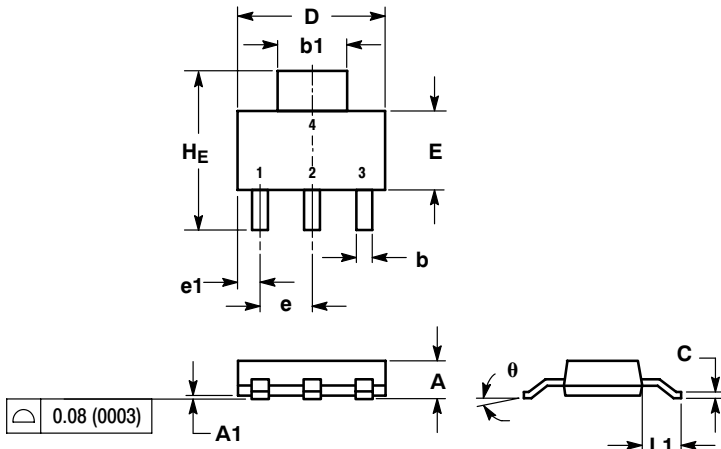


Figure 4. "ON" Voltages

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PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE L



NOTES:

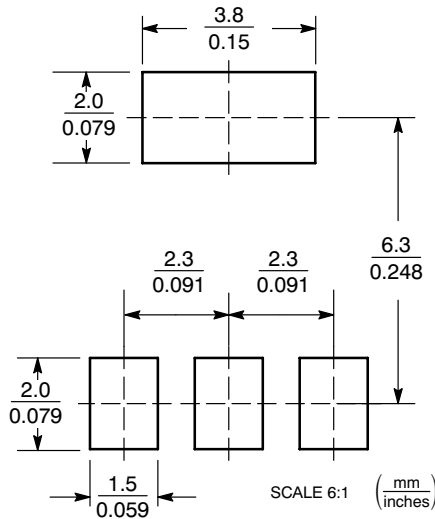
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L1	1.50	1.75	2.00	0.060	0.069	0.078
H _E	6.70	7.00	7.30	0.264	0.276	0.287
Ø	0°	-	10°	0°	-	10°


STYLE 1:

- PIN 1:
1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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